

### **General Description**

The WSF7N65 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF7N65 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

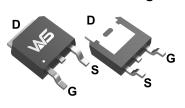
### **Product Summery**

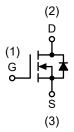
BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
650V	1200mΩ	7A

### **Applications**

- AC/DC Power Conversion in Switched Mode Power Supplies (SMPS).
- Uninterruptible Power Supply(UPS)
- Adapter.

### **TO-252-2L Pin Configuration**





### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	650	V
$V_{GS}$	Gate-Source Voltage	±30	V
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1.5</sup>	7	Α
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1.5</sup>	2.8	Α
I <sub>DM</sub>	Pulsed Drain Current <sup>1.2.5</sup>	21	Α
EAS	Single Pulse Avalanche Energy <sup>1</sup>	17.5	mJ
P <sub>D</sub>	Total Power Dissipation <sup>1,5</sup>	69	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	$^{\circ}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>0JA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		1.8	°C/W



### Electrical Characteristics (T<sub>J</sub>=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	650			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃ , I <sub>D</sub> =250uA		0.6		V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =2A		1200	1450	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> . In =250uA	2.5	3.5	4.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	VGS-VDS , ID -250UA		-4.57		mV/℃
	Drain Source Loakage Current	$V_{DS}$ =520V , $V_{GS}$ =0V , $T_J$ =25 $^{\circ}$ C			1	uA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =520V , V <sub>GS</sub> =0V , T <sub>J</sub> =150℃			200	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 30 V$ , $V_{DS}$ = $0 V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =40V , I <sub>D</sub> =3.5A		5		S
Qg	Total Gate Charge (10V)			12.8	16.6	
Q <sub>gs</sub>	Gate-Source Charge V <sub>DS</sub> =520V , V <sub>GS</sub> =10V , I <sub>D</sub> =2A			3		nC
Q <sub>gd</sub>	Gate-Drain Charge			5.1		
T <sub>d(on)</sub>	Turn-On Delay Time			10		
T <sub>r</sub>	Rise Time	V <sub>DD</sub> =400V , V <sub>GS</sub> =10V ,		22.5		
T <sub>d(off)</sub>	Turn-Off Delay Time	$R_G=6\Omega$ , $I_D=4A$ .		13		ns
T <sub>f</sub>	Fall Time			15		
C <sub>iss</sub>	Input Capacitance			225	290	
Coss	Output Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , f=1MHz		200	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			1.5		

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,2,5</sup>	V =V =0V Force Current			7	Α
I <sub>SM</sub>	Pulsed Source Current <sup>1,2</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			16	Α
V <sub>SD</sub>	Diode Forward Voltage <sup>1</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =4A , T <sub>J</sub> =25℃		0.95	1.3	V
t <sub>rr</sub>	Reverse Recovery Time			454		nS
Q <sub>rr</sub>	Reverse Recovery Charge	IF=7A , dI/dt=40A/µs , T <sub>J</sub> =25℃		2076		nC

### Notes:

Note 1: limited by maximum junction temperature.

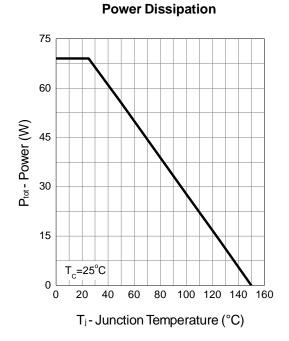
Note 2 : Bond wire current limit. Note 3 :  $V_{DS}$ =520V,  $I_{D}$ =4A.

Note 4 :  $I_D$ =0.5A,  $V_{DD}$ =50V,  $T_j$ =25°C.

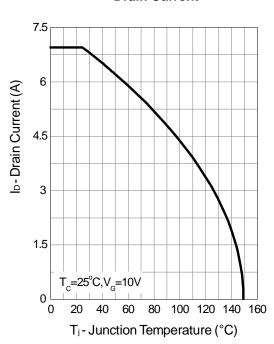
Note 5: Repetitive Rating: Pulse width limited by maximum junction temperature.



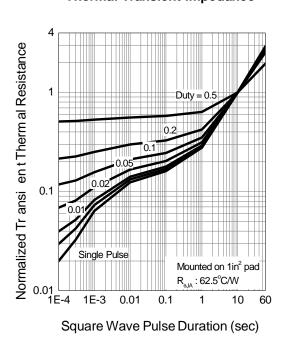
### **Typical Characteristics**



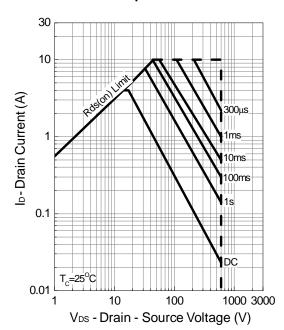
### **Drain Current**



### **Thermal Transient Impedance**

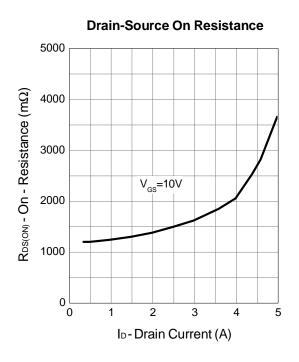


### Safe Operation Area



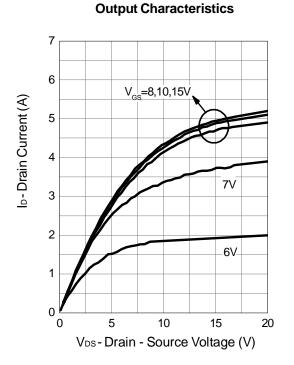


### **Typical Characteristics (Cont.)**



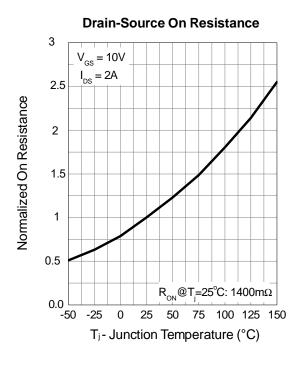
## BVDSS vs Junction Temperature 1.6 1.4 1.2 1.0 1.2 0.8 0.4 -50 -25 0 25 50 75 100 125 150 V<sub>SD</sub> - Source - Drain Voltage (V)

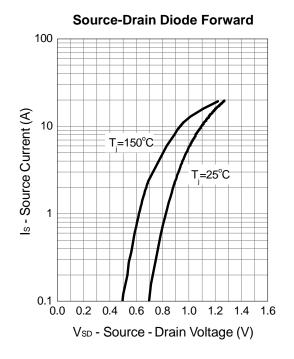
# V<sub>GS(th)</sub> vs Junction Temperature 1.2 1.1 1.0 1.0 0.6 -50 -25 0 25 50 75 100 125 150 V<sub>GS</sub> - Gate-Source Voltage (V)



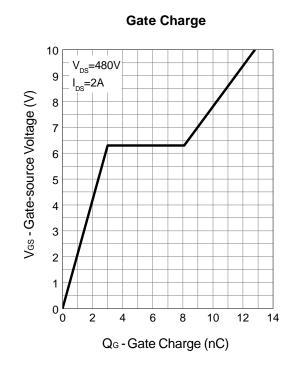


### **Typical Characteristics (Cont.)**



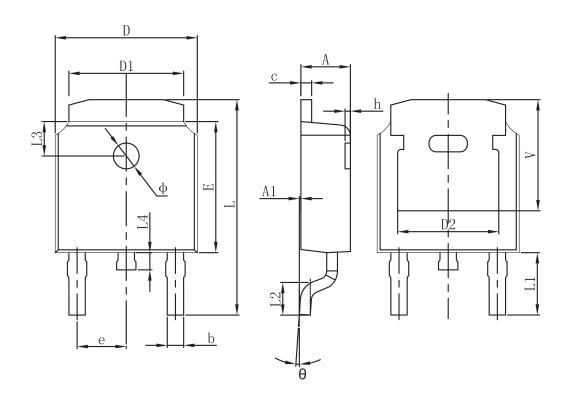


### Capacitance 10000 Frequency=1MHz 1000 C - Capacitance (pF) Ciss 100 Coss 10 Crss-1 <sup>L</sup> 20 25 10 15 30 35 V<sub>DS</sub> - Drain - Source Voltage (V)





## **Packaging information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	REF.	0.190	REF.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063 REF.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207 REF.		



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